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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/601,938	06/23/2003	Krishna K. Nair	9180-29	7585

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EXAMINER	
OWENS, BETH E	

ART UNIT	PAPER NUMBER
2824	

DATE MAILED: 09/21/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary	Application No.	Applicant(s)	
	10/601,938	NAIR ET AL.	
	Examiner	Art Unit	
	Beth E. Owens	2824	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 1 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

1)☐ Responsive to communication(s) filed on _____.

2a)☐ This action is **FINAL**. 2b)☐ This action is non-final.

3)☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

4)☒ Claim(s) 1-93 is/are pending in the application.

4a) Of the above claim(s) _____ is/are withdrawn from consideration.

5)☐ Claim(s) _____ is/are allowed.

6)☐ Claim(s) _____ is/are rejected.

7)☐ Claim(s) _____ is/are objected to.

8)☒ Claim(s) 1-93 are subject to restriction and/or election requirement.

Application Papers

9)☐ The specification is objected to by the Examiner.

10)☐ The drawing(s) filed on _____ is/are: a)☐ accepted or b)☐ objected to by the Examiner.

Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).

Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).

11)☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

12)☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).

a)☐ All b)☐ Some * c)☐ None of:

1.☐ Certified copies of the priority documents have been received.

2.☐ Certified copies of the priority documents have been received in Application No. _____.

3.☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

1) ☐ Notice of References Cited (PTO-892)
2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
3) ☐ Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date _____.
4) ☐ Interview Summary (PTO-413) Paper No(s)/Mail Date. _____ .
5) ☐ Notice of Informal Patent Application (PTO-152)
6) ☐ Other: _____.

Election/Restrictions

1. Restriction to one of the following inventions is required under 35 U.S.C. 121:

I. Claims 1-31, 70-81 and 88-93, drawn to the method of manufacturing, classified in class 438, subclass 597+.

II. Claims 32-69 and 82-87, drawn to the device, classified in class 257, subclass 734+.

The inventions are distinct, each from the other because of the following reasons:

Inventions Group I and Group II are related as the process of making and the product made. The inventions are distinct if either or both of the following can be shown: (1) that the process as claimed can be used to make other and materially different product or (2) that the product as claimed can be made by another and materially different process [MPEP §806.05 (f)]. For example, the solder layer of the manufacturing method does not have to have a rounded surface opposite the conductive shunt as claimed for the device. Because these inventions are distinct for the reason given above and have acquired a separate status in the art as shown by their different classification, restriction for examination purposes as indicated is proper.

Applicant is advised that the reply to this requirement to be complete must include an election of the invention to be examined even though the requirement be traversed (37 CFR 1.143).

2. This application contains claims directed to the following patentably distinct species of the claimed invention, found in the Summary of the Invention section:

Species 1: method of forming an electronic structure may include forming a seed layer on an electronic substrate, and forming a conductive shunt layer on portions of the seed layer wherein portions of the seed layer are free of the shunt layer. A conductive barrier layer may be formed on the conductive shunt layer opposite the seed layer wherein the shunt layer comprises a first material and wherein the barrier layer comprises a second material different than the first material. Moreover, a solder layer may be formed on the barrier layer opposite the shunt layer wherein the solder layer comprises a third material different than the first and second materials. After forming the solder layer, portions of the seed layer free of the solder layer may be removed. The barrier layer may also include a passivation layer, such as a layer of gold, thereon. The seed layer may include an adhesion layer of a fourth material different than the first material of the conductive shunt layer. In addition, the seed layer may include a plating conduction layer on the

adhesion layer opposite the substrate, and the plating conduction layer may include a layer of the first material of the conductive shunt layer.

Species 2: After forming the seed layer, a mask layer may be formed on the seed layer wherein the mask layer has a pattern exposing a surface portion of the seed layer. Accordingly, the conductive shunt layer can be formed by plating the conductive shunt layer on the exposed surface portion of the seed layer, the conductive barrier layer can be formed by plating the conductive barrier layer on the conductive shunt layer, and the solder layer can be formed by plating the solder layer on the respective barrier layer.

Species 3: Forming the electronic device can also include forming a conductive pad on a substrate, and forming an insulating layer on the substrate and on the conductive pad wherein the insulating layer has a via therein so that a portion of the conductive pad opposite the substrate is free of the insulating layer. More particularly, the seed layer can be on the insulating layer, on sidewalls of the via and on the portions of the conductive pad free of the insulating layer, and the conductive shunt layer can be on the seed layer opposite the portions of the conductive pad free of the insulating layer, opposite the sidewalls of the via and opposite portions of the insulating layer adjacent the via.

Species 4: forming a conductive pad on a substrate, and forming an insulating layer on the substrate and on the conductive pad wherein the

insulating layer has a via therein so that a portion of the conductive pad opposite the substrate is free of the insulating layer. A conductive shunt layer may be formed on the portion of the conductive pad free of the insulating layer, on sidewalls of the via and on surface portions of the insulating layer surrounding the via opposite the substrate and the conductive pad. A conductive barrier layer can be formed on the conductive shunt layer opposite the conductive pad and the insulating layer wherein the shunt layer and the barrier layer comprise different materials. In addition, a solder layer can be formed on the barrier layer opposite the shunt layer wherein the solder layer and the barrier layer comprise different materials. Before forming the conductive shunt layer, a seed layer may be formed on the conductive pad and on the insulating layer so that the seed layer is between the conductive shunt layer and the portion of the conductive pad free of the insulating layer and so that the seed layer is between the conductive shunt layer and the insulating layer. The seed layer may include an adhesion layer of a material different than that of the conductive shunt layer. In addition, the seed layer may include a plating conduction layer on the adhesion layer opposite the substrate, wherein the plating conduction layer and the conductive shunt layer comprise a common material. Moreover, the conductive shunt layer, the conductive barrier layer, and the solder layer may be on portions of the seed layer, and portions of the seed layer may be free of the conductive shunt layer, the

conductive barrier layer, and the solder layer. After forming the solder layer, portions of the seed layer free of the conductive shunt layer, free of the conductive barrier layer, and free of the solder layer may be removed.

Species 5: After forming the seed layer, a mask layer may be formed on the seed layer, wherein the mask layer has a pattern exposing a surface portion of the seed layer opposite the portion of the conductive pad free of the insulating layer, opposite sidewalls of the via and opposite surface portions of the insulating layer surrounding the via. Accordingly, forming the conductive shunt layer may include plating the conductive shunt layer on the exposed portion of the seed layer, forming the conductive barrier layer may include plating the conductive barrier layer on the conductive shunt layer, and forming the solder layer may include placing the solder layer on the barrier layer. The mask layer may be removed after forming the solder layer, and portions of the seed layer surrounding the conductive shunt layer may be removed after removing the mask layer.

Species 6: forming an electronic structure may include forming a primary conductive trace on an electronic substrate, the primary conductive trace having a first width, and forming a conductive pad on the electronic substrate, the conductive pad having a second width greater than the first width. An electrical coupling may also be formed between the primary conductive trace and the conductive pad, wherein the electrical coupling

provides at least two separate current flow paths between the primary conductive trace and the conductive pad. The electrical coupling may include a flared coupling extending from the primary conductive trace to the conductive pad and having a perforation therein. The electrical coupling may include first and second traces extending from the primary conductive trace to spaced apart portions of the conductive pad. The first and second traces extend to opposite sides of the conductive pad.

Species 7: In an alternative, the conductive pad may be circular, and the first and second traces may extend tangentially from different portions of the circular conductive pad and meet at the primary conductive trace. The first and second traces may extend from the circular pad in parallel directions and turn to meet at the primary conductive trace, and/or the electrical coupling may include a third trace extending from the primary conductive trace to the conductive pad between the first and second traces. Moreover, the third trace may have a width that is less than a width of either of the first and second traces.

Species 8: In addition, a solder layer may be formed on the conductive pad, and a second electronic substrate may be provided on the solder layer wherein at least one of the first and second traces can be coupled to the conductive pad adjacent to a portion of the solder layer subject to compressive stress.

Species 9: In addition, an insulating layer may be formed on the electronic substrate, on the conductive trace, on the conductive pad, and on the electrical coupling, wherein the insulating layer has a via therein so that a portion of the conductive pad is free of the insulating layer. The electronic substrate may include a semiconductor substrate, a contact pad on the semiconductor substrate, and an insulating layer on the semiconductor substrate and the contact pad, and the insulating layer may have a via therein so that a portion of the contact pad is free of the insulating layer. Moreover, the conductive trace, the conductive pad, and the electrical coupling may be on the insulating layer opposite the substrate, and the conductive trace may be electrically coupled with the contact pad through the via.

The following species (claims 88-92) is not described in the Summary of the Invention section, but is described in the Detailed Description section, page 22, lines 17+:

Species 10: Electronic structures according to embodiments of the present invention may thus include a primary conductive trace on an electronic substrate wherein the primary conductive trace has a first width and a conductive pad on the electronic substrate wherein the conductive pad has a second width greater than the first width. An electrical coupling between the primary conductive trace and the conductive pad may provide different

resistances to current flow across a width thereof. Different resistances may be provided, for example, by providing an opening in the electrical coupling such as the perforation 407 illustrated in Figure 4A..

If Applicant elects the Inventions of Group I (method of manufacturing), Applicant is required under 35 U.S.C. 121 to elect a single disclosed species for prosecution on the merits to which the claims shall be restricted if no generic claim is finally held to be allowable. Currently, Claims 1, 16, 70 or 88 could be generic dependent upon the Species elected.

Applicant is advised that a reply to this requirement must include an identification of the species that is elected consonant with this requirement, and a listing of all claims readable thereon, including any claims subsequently added. An argument that a claim is allowable or that all claims are generic is considered nonresponsive unless accompanied by an election.

Upon the allowance of a generic claim, applicant will be entitled to consideration of claims to additional species which are written in dependent form or otherwise include all the limitations of an allowed generic claim as provided by 37 CFR 1.141. If claims are added after the election, applicant must indicate which are readable upon the elected species. MPEP § 809.02(a).

Should applicant traverse on the ground that the species are not patentably distinct, applicant should submit evidence or identify such evidence

now of record showing the species to be obvious variants or clearly admit on the record that this is the case. In either instance, if the examiner finds one of the inventions unpatentable over the prior art, the evidence or admission may be used in a rejection under 35 U.S.C. 103(a) of the other invention.

Conclusion

3. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Beth E. Owens, Ph.D. whose telephone number is 571.272.1882.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Richard Elms, can be reached on 571.272.1869. The fax phone number for the organization where this application or proceeding is assigned is 703.872.9306 for official communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 571.272.2800.

BEO

BEO 09.09.04

MICHAEL S. LEBENTRITT
PRIMARY EXAMINER